PCN Number:			20160408001					PCN Date:			4/12/2	016			
Title:QualificationSelect Device		ion o vices	of Additional Fab (RFAB) and Additional Assembly/Test (TI Clark) sites						for						
Customer Contact:			:: <u>P</u>	PCN Manager De			ept:	pt: Quality Services					-		
Proposed 1 st Ship Da			Date	ite: 7/12/2016		016	Estin	Estimated Sample A			vailability: Prov		ided upoi Jest	n	
Char	nge	Туре:													
Assembly Site				Assembly Pro				cess 🛛 🖾 Assem				ibly Materials			
	Desi	gn			Electrical Spe			cification			Mechanical Specification				
Test Site					Packing/Ship			ping/Labeling			Test Process				
Wafer Bump Site			te		Wafer Bump I			Material			Wafer Bump Process				
Wafer Fab Site					Wafer Fab Ma			iterials			Wafer Fab Process				
					Part number change										
1						P	CN D	etails							
Desc	cript	tion of Cha	ange	:				1.0. 1.				1 1.1.1.1			1 77
l exa	s Ins	struments	is ple	ased	to ann	iounce th	ie qua	alification	of H		as an	additio	onal fa	ab site ar	nd II
Clark	(as	an additior	al as	semp	ly/test	site for	the de	evices iis	tea	belo	w. Dev	ice co	nstru	ction	
unie	rence	es betweer	i the	vario	us site	s are as	IOHOW	/S:							
	Wh	at (Packa	ae D)esia	nator		ΜΙΑ		CRS			TI Clau		ark	1
	Мо	unt Compo	und ((RHB)		42	4205846		SID#435143		143	4	4207768		
	Мо	unt Compo	und (RGZ			n/a	S	SID#	435	143	4	4207	123	
							1 -				-				1
	Fab	Details													
	Current Fab Site		P	Process		Wafe Diamet	Wafer Ac iameter F		nal te	I Process		s Wafer Diameter			
ľ	DP1DM5			C05 200 m		m	RFAB		C05		30	0 mm			
Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ.															
Reason for Change:															
Continuity of Supply															
Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):															
None															
Anticipated impact on Material Declaration															
No Impact to the Material Declaration		าe ation		Material Declarations or Product Content reports are driven from production data and will be available following the production release. Upon production release the revised reports can be obtained from the <u>TI ECO website</u> .						m					
Changes to product identification resulting from this PCN:															
Assembly Site Ass		Asse	Assembly Site Origin		gin (22L)	Asse	mbly Cou	y Country Cod		e (21L)		Assem	bly City		
	TI Malaysia			MLA			MYS						Kuala	Lumpur	
	Carsem			CRS			MYS						Jelapang		
TI Clark		1	OAB			1	PHL			Angeles City					

Fab Sites			
Chip Sites	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DP1DM5	DM5	USA	Dallas
New	· · · · · ·		
Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
RFAB	RFB	USA	Richardson
Sample product shipping	label (not actual produ	<pre>vict label) v) \$N74L\$07N\$R vice and vice an</pre>	

(P) (2P) REV:

(20L) CSO: SHE (22L) ASO: MLA

(V) 0033317 (21L) CCO:USA

(23L) ACO: MYS

Topside Device marking: Assembly site code for MLA= K Assembly site code for CRS = WAssembly site code for QAB = I

39

(L)T0:1750

5A

Product Affected TLV320AIC3004IRHBR TLV320AIC3105IRHBR TLV320AIC3106IRGZR TLVAIC3105IRHBRG4 TLV320AIC3004IRHBT TLV320AIC3105IRHBT TLV320AIC3106IRGZT



OPT: ITEM:

LBL:

TI Information Selective Disclosure

Qualification Report

TLV320AIC3106/5/6RGZ in RFAB and Clark (release the G2TIAIC39A die in Clark) Approve Date 05-Apr-2016 **Product Attributes**

Attributes	Qual Device: TLV320AIC3106IRGZR	QBS Process Reference: VSP6825BZRC	QBS Package Reference: SN65LVCP40RGZ	QBS Package Reference: TPS62402DRCR _CU_WIRE	
Assembly Site	CLARK-AT	PHI	CLARK-AT	CLARK-AT	
Package Family	QFN	JRBGA	QFN	SON	
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	
Wafer Fab Supplier	RFAB	HIJI, RFAB	FFAB	FFAB	
Wafer Process	1118C05	1833C05, LBC4	BICOM3	3370A12	

QBS: Qual By Similarity

- Qual Device TLV320AIC3106IRGZR is qualified at LEVEL2-260C

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: TLV320AIC3106IRGZR	QBS Process Reference: VSP6825BZRC	QBS Package Reference: SN65LVCP40RGZ	QBS Package Reference: TPS62402DRCR _CU_WIRE
AC	Autoclave 121C	96 Hours	-	-	1/77/0	1/77/0
ED	Electrical Characterization	Per Datasheet Parameters	Pass	-	-	-
HAST	Biased HAST,130C/85%RH	96 Hours	-	3/230/0	1/77/0	-
HTOL	Life Test, 140C	480 Hours	-	3/231/0	-	-
HTOL	Life Test, 155C	240 Hours	-	-	1/77/0	-
HTSL	High Temp. Storage Bake, 170C	420 Hours	-	3/231/0	1/77/0	1/77/0
PD	Physical Dimensions		-	-	1/5/0	1/5/0
TC	Temperature Cycle, - 65/150C	500 Cycles	-	3/231/0	1/77/0	1/77/0
TS	Thermal Shock, - 65/150C	500 Cycles	-	-	-	1/77/0
WBP	Bond Pull	Wires	1/76/0	-	1/76/0	1/76/0
WBS	Wire Bond Shear	Wires	1/76/0	-	1/76/0	1/76/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
 The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
 The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TTs external Web site: http://www.ti.com/ Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com